

1 1200 1 -2 4
 1 120 - 1



Description

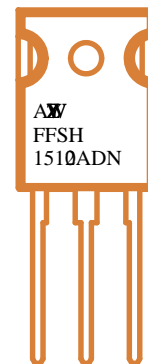
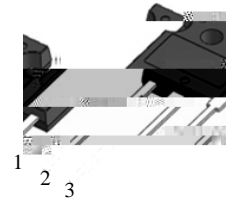
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 80 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb-Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



A -Assembly Plant Code
 W -Date Code (Year & Week)
 Z -Lot Code
 FFSH1510ADN -Specific Device Code

FFSH15120ADN-F155

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (per leg)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		1200	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		80	mJ
I_F	Continuous Rectified Forward Current @ $T_C < 153^\circ\text{C}$		8* / 15**	A
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}$, 10 μs	560	A
		$T_C = 150^\circ\text{C}$, 10 μs	500	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3$ ms	80	A
$I_{F,RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3$ ms	36	A
P_{TOT}	Power Dissipation	$T_C = 25^\circ\text{C}$	110	W
		$T_C = 150^\circ\text{C}$	19	W
T_J, T_{STG}	Operating and Storage Temperature Range			

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